



TWTLSEMI

TL-BCX56-16

SOT-89-3L Plastic-Encapsulate Transistors (NPN)

Features

- PNP Complements to BCX53
- Low Voltage
- High Current



SOT-89-3L

Absolute Maximum Ratings($T_A=25^\circ\text{C}$)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	1	A
I_B	Base Current	0.1	A
I_{BM}	Peak base Current ($t_p < 1\text{ms}$)	0.2	A
P_c	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	250	$^\circ\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction And Storage Temperature Range	-55 ~ +150	$^\circ\text{C}$
T_{opr}	Operation Temperature Range	-25~+125	$^\circ\text{C}/\text{W}$

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=100\mu\text{A}, I_E=0$	100			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=10\text{mA}, I_B=0$	80			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=10\mu\text{A}, I_C=0$	5			V
I_{CBO}	Collector cut-off current	$V_{CB}=30\text{V}, I_E=0$			0.1	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5\text{V}, I_C=0$			0.1	μA
$h_{FE(1)}$	DC current gain	$V_{CE}=2\text{V}, I_C=5\text{mA}$	40			
$h_{FE(2)}$		$V_{CE}=2\text{V}, I_C=150\text{mA}$	63		250	
$h_{FE(3)}$		$V_{CE}=2\text{V}, I_C=0.5\text{A}$	25			
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C=0.5\text{A}, I_B=50\text{mA}$			0.5	V
V_{BE}	Base -emitter voltage	$V_{CE}=2\text{V}, I_C=0.5\text{A}$			1	V
f_T	Transition frequency	$V_{CE}=5\text{V}, I_C=10\text{mA}, f=100\text{MHz}$		130		MHz

Ordering information

Product ID	Pack	Naming rule	Marking	$h_{FE(1)}$	Qty(PCS)
BCX56-16	SOT-89-3L	<div style="border: 1px solid black; padding: 2px; text-align: center;"> BCX56-16 <small>产品名称 product name</small> </div>	BL	100-250	1000

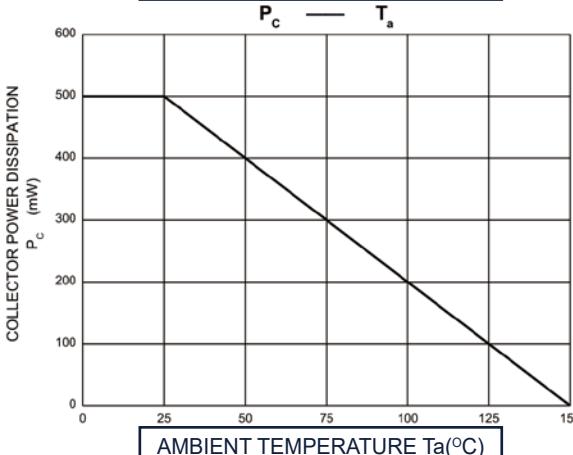
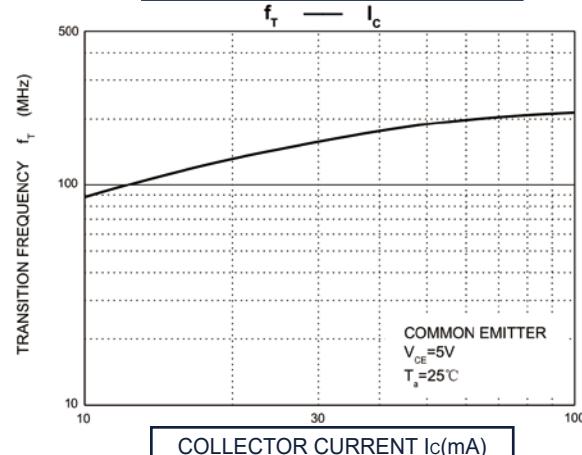
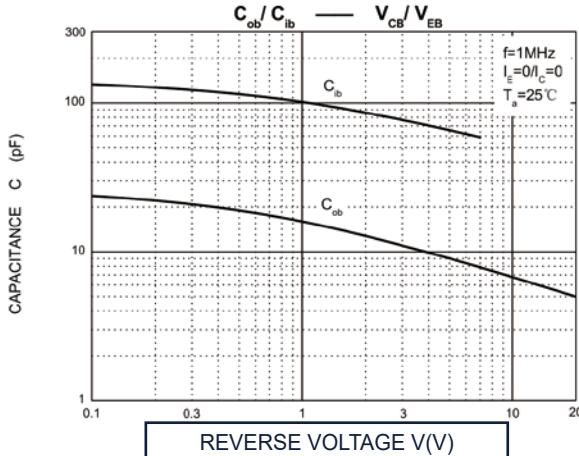
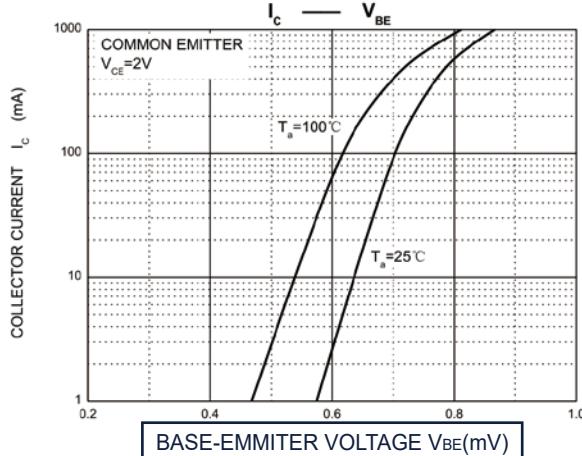
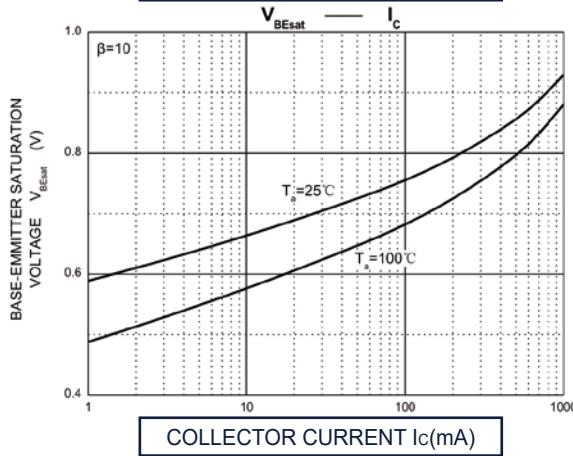
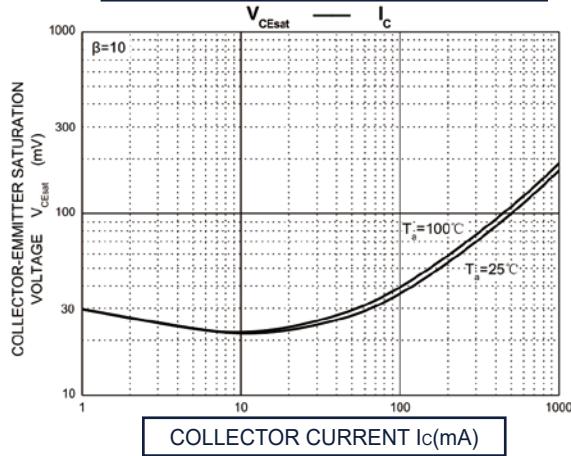
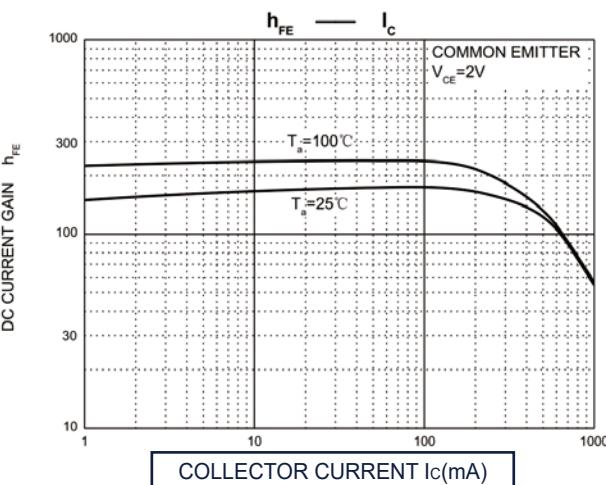
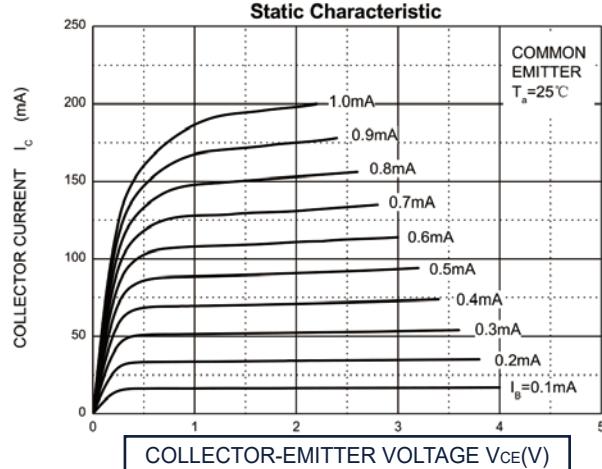


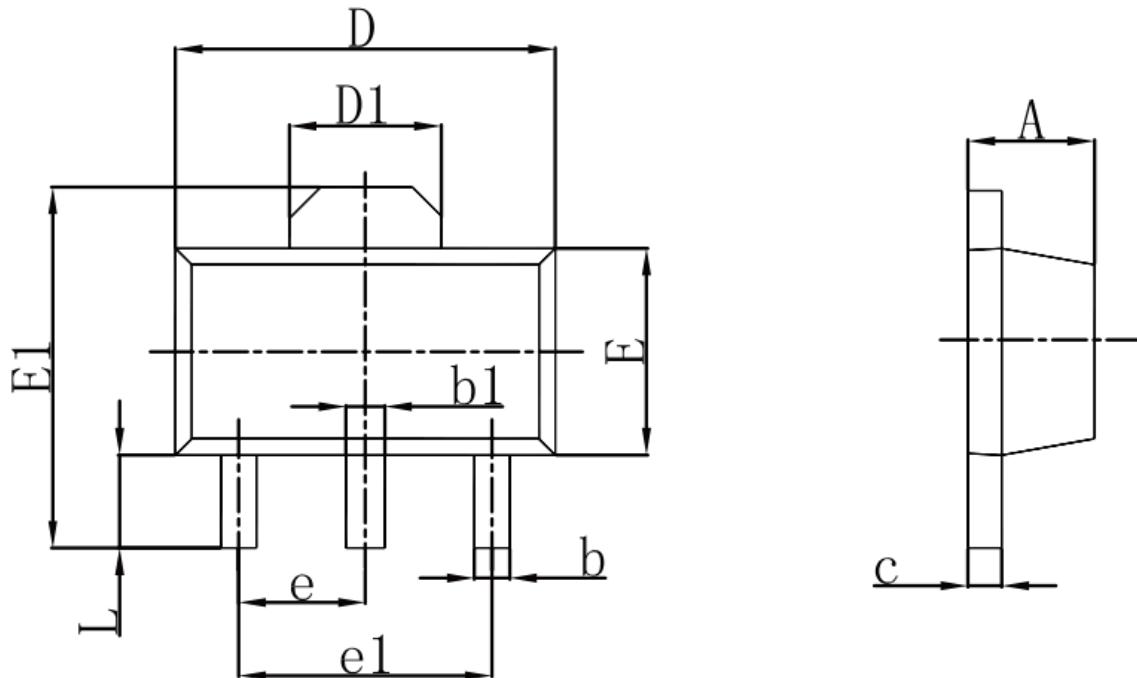
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Typical Characteristics



SOT-89-3L Package Outline Dimensions


Symbol	Dimensions in Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047